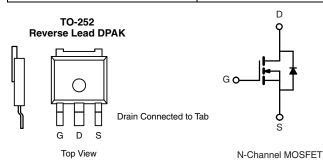


Automotive N-Channel 30 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	30				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0060				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0085				
I _D (A)	50				
Configuration	Single				



FEATURES

- TrenchFET® Power MOSFET
- AEC-Q101 Qualified
- 100 % Rq and UIS Tested
- Material categorization:
 For definitions of compliance please see www.freescale.net.cn



ORDERING INFORMATION	
Package	TO-252 Reverse Lead DPAK
Lead (Pb)-free and Halogen-free	SQR50N03-06P-GE3

PARAMETER		SYMBOL	LIMIT	UNIT
Drain-Source Voltage		V_{DS}	30	V
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current ^a	T _C = 25 °C	J _	50	
	T _C = 125 °C		50	
Continuous Source Current (Diode Conduction) ^a		I _S	50	Α
ulsed Drain Current ^b		I _{DM}	200	
Single Pulse Avalanche Current	1 0.1 ml 1	I _{AS}	45	
Single Pulse Avalanche Energy	L = 0.1 mH	E _{AS}	101	mJ
Mariana Baran Biratadia b	T _C = 25 °C	_C = 25 °C	83	W
Maximum Power Dissipation ^b	T _C = 125 °C	P_{D}	27	VV
Operating Junction and Storage Temperatu	T _J , T _{stg}	- 55 to + 175	°C	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	50	°C/W
Junction-to-Case (Drain)		R_{thJC}	1.8	C/VV

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- c. When mounted on 1" square PCB (FR-4 material).



SQR50N03-06PAutomotive N-Channel 30 V (D-S) 175 °C MOSFET

PARAMETER	SYMBOL	TES	TEST CONDITIONS		TYP.	MAX.	UNIT
Static						·	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		30	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		2.0	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		V _{GS} = 0 V	V _{DS} = 30 V	-	-	1	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 30 V, T _J = 125 °C	-	-	50	μΑ
		V _{GS} = 0 V	V _{DS} = 30 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 V$	50	-	=-	Α
		V _{GS} = 10 V	I _D = 20 A	-	0.0047	0.0060	Ω
Due in Course On Chata Basistanas		V _{GS} = 10 V	I _D = 20 A, T _J = 125 °C	-	-	0.0090	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 20 A, T _J = 175 °C	-	-	0.0107	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.0067	0.0085	
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		-	74	-	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	3222	4030	pF
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	563	705	
Reverse Transfer Capacitance	C _{rss}			-	241	300	
Total Gate Charge ^c	Qg			-	25.2	38	nC
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 4.5 V	$V_{DS} = 15 \text{ V}, I_{D} = 50 \text{ A}$	-	9.1	-	
Gate-Drain Charge ^c	Q _{gd}	1		-	9.4	-	
Gate Resistance	R_g	f = 1 MHz		0.5	1.6	2.8	Ω
Turn-On Delay Time ^c	t _{d(on)}	V_{DD} = 15 V, R_L = 0.3 Ω I_D \cong 50 A, V_{GEN} = 10 V, R_g = 1 Ω		-	10	15	
Rise Time ^c	t _r			-	10	15	- ns
Turn-Off Delay Time ^c	t _{d(off)}			-	26	39	
Fall Time ^c	t _f			-	9	14	
Source-Drain Diode Ratings and Chara	acteristics ^b				•		
Pulsed Current ^a	I _{SM}			-	-	200	Α
Forward Voltage	V _{SD}	I _F = 85 A, V _{GS} = 0 V		-	1	1.5	V

Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

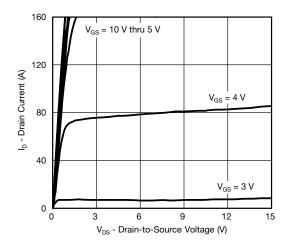
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



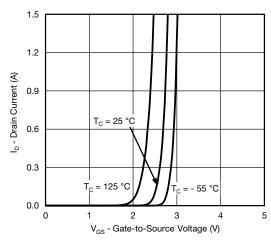
SQR50N03-06P Automotive N-Channel

30 V (D-S) 175 °C MOSFET

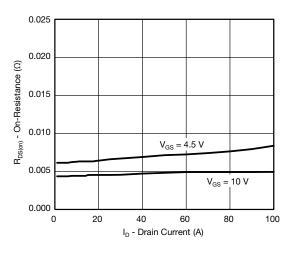
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



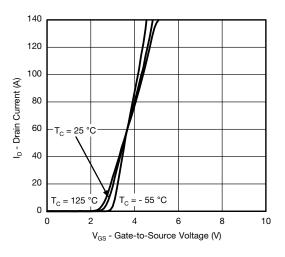
Output Characteristics



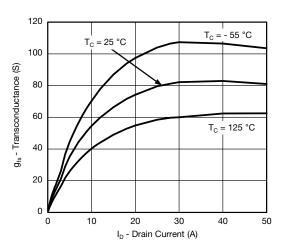
Transfer Characteristics



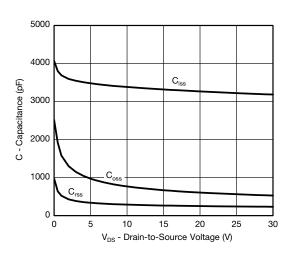
On-Resistance vs. Drain Current



Transfer Characteristics



Transconductance

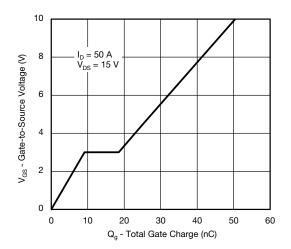


Capacitance

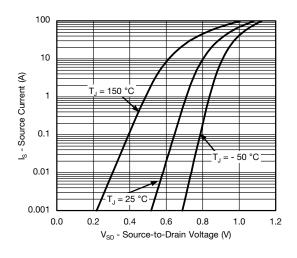


Automotive N-Channel 30 V (D-S) 175 °C MOSFET

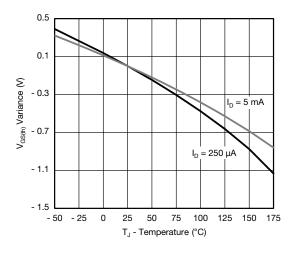
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



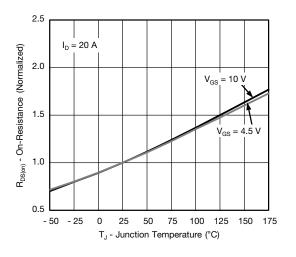
Gate Charge



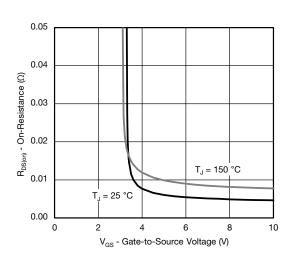
Source Drain Diode Forward Voltage



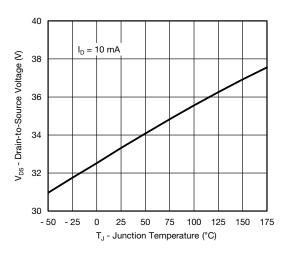
Threshold Voltage



On-Resistance vs. Junction Temperature



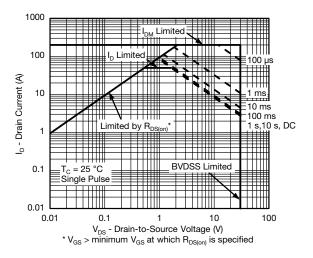
On-Resistance vs. Gate-to-Source Voltage



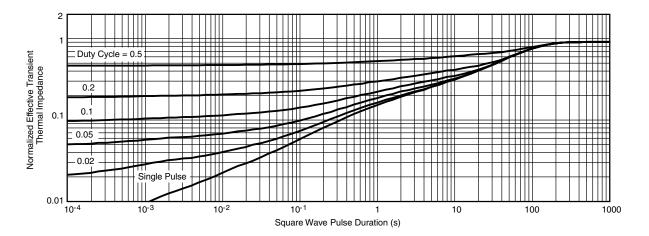
Drain Source Breakdown vs. Junction Temperature

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



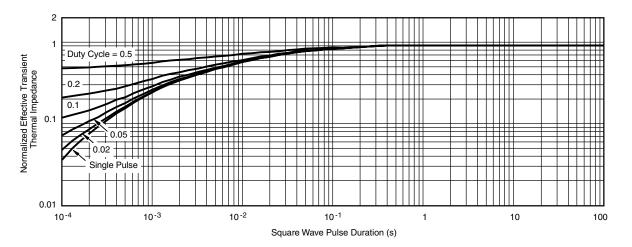
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient

SQR50N03-06P Automotive N-Channel 30 V (D-S) 175 °C MOSFET

THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



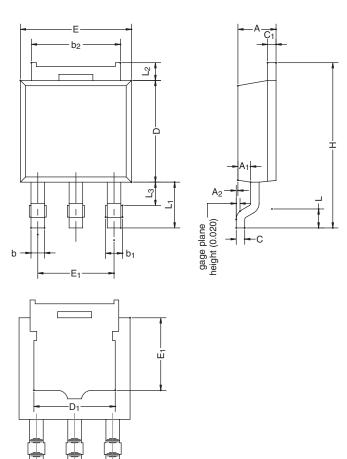
Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Automotive N-Channel 30 V (D-S) 175 °C MOSFET

TO-252 REVERSE LEAD CASE OUTLINE



	MILLIMETERS		INC	HES		
DIM.	MIN.	MAX.	MIN.	MAX.		
Α	2.23	2.33	0.088	0.092		
A ₁	0.64	0.89	0.025	0.035		
A ₂	0.03	0.23	0.001	0.009		
b	0.71	0.88	0.028	0.035		
b ₁	0.76	1.14	0.030	0.045		
b ₂	5.23	5.44	0.206	0.214		
С	0.46	0.58	0.018	0.023		
C ₁	0.46	0.58	0.018	0.023		
D	5.97	6.22	0.235	0.245		
D ₁	4.49	5.00	0.177	0.197		
Е	6.48	6.73	0.255	0.265		
E ₁	4.32	-	0.170	-		
е	2.28 BSC		0.090	BSC		
e ₁	4.57	BSC	0.180	BSC		
Н	9.65	10.41	0.380	0.410		
L	1.40	1.78	0.055	0.070		
L ₁	2.74 BSC		0.108	BSC		
L ₂	0.89	1.27	0.035	0.050		
L ₃	1.15	1.52	0.040	0.060		
ECN: T-08706-Rev. B, 29-Sep-08						
DWG: 5894						

Note

Dimension L₃ for reference only.



SQR50N03-06P Automotive N-Channel 30 V (D-S) 175 °C MOSFET

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